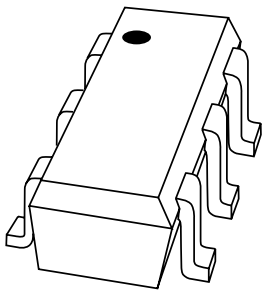
DATA SHEET



BGA2012
1900 MHz high linear low noise amplifier

Product specification
Supersedes data of 2000 Sep 06

2000 Dec 04

Philips
Semiconductors

PHILIPS

1900 MHz high linear low noise amplifier BGA2012

FEATURES

- Low current, low voltage
- High linearity
- High power gain
- Low noise
- Integrated temperature compensated biasing
- Control pin for adjustment bias current.

APPLICATIONS

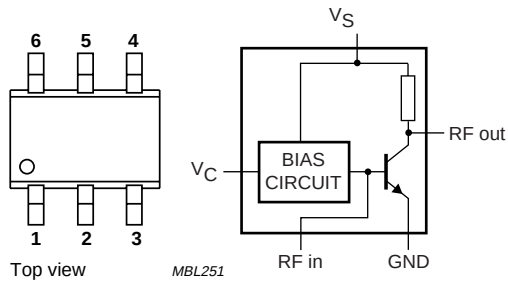
- RF front end
- Low noise amplifiers, e.g. CDMA, PHs, Dect, etc.

DESCRIPTION

Silicon Monolitic Microwave Integrated Circuit (MMIC) amplifier consisting of an NPN double polysilicon transistor with integrated biasing for low voltage applications in a 6-pin SOT363 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	RF in
2	V_C
3	V_S
4	RF out
5, 6	GND



Marking code: A6-

Fig.1 Simplified outline (SOT363) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_S	DC supply voltage	RF input AC coupled	3	4.5	V
I_S	DC supply current		7.5	–	mA
I_C	DC control current	$V_C = V_S$	0.11	–	mA
$\|s_{21}\|^2$	insertion power gain	in application circuit, see Fig.2; f = 1900 MHz	16	–	dB
NF	noise figure	I_S = 7 mA; f = 1900 MHz	1.7	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_S	DC supply voltage	RF input AC coupled	–	4.5	V
V_C	voltage on control pin		–	V_S	V
I_S	supply current	forced by DC voltage on RF input	–	15	mA
I_C	control current		–	0.25	mA
P_{tot}	total power dissipation	$T_s \leq 100$ °C	–	70	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to solder point	P_{tot} = 135 mW; $T_s \leq 100$ °C	350	K/W

CHARACTERISTICS

RF input AC coupled; V_S = 3 V; I_S = 7 mA; f = 1900 MHz; T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_S	supply current		5	7.5	10	mA
I_C	control current		–	0.11	–	mA
$R_{L\ IN}$	return losses input	typical application; see Fig.2	–	–11	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	–20	–	dB
		high IP3 (see Fig.2; stripline = 0.5 mm)	–	–14	–	dB
$R_{L\ OUT}$	return losses output	typical application; see Fig.2	–	–9	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	–10	–	dB
		high IP3 (see Fig.2; stripline = 0.5 mm)	–	–8	–	dB
$\lvert s_{21}\rvert^2$	insertion power gain	typical application (see Fig.2)	–	14	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	16	–	dB
		high IP3 (see Fig.2; stripline = 0.5 mm)	–	14	–	dB
NF	noise figure	typical application; see Fig.2; I_S = 7 mA	–	1.7	–	dB
		high IP3 (see Fig.2; stripline = 0 mm)	–	2.2	–	dB
		high IP3 (see Fig.2; stripline = 0.5 mm)	–	2.3	–	dB
$IP3_{in}$	input intercept point	typical application; see Fig.2	–	–7	–	dBm
		high IP3 (see Fig.2; stripline = 0 mm)	–	7	–	dBm
		high IP3 (see Fig.2; stripline = 0.5 mm)	–	10	–	dBm

APPLICATION INFORMATION

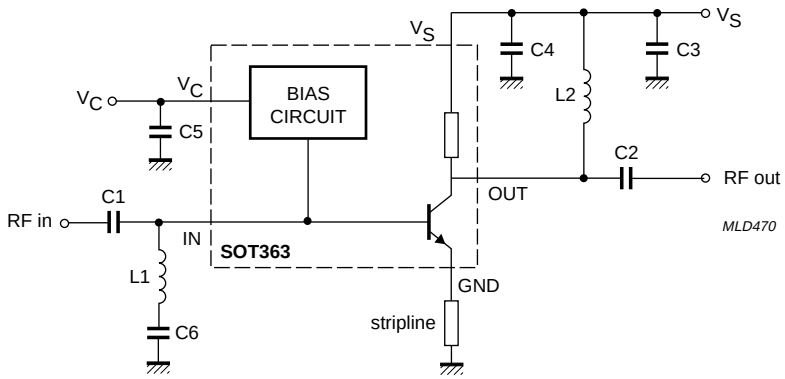


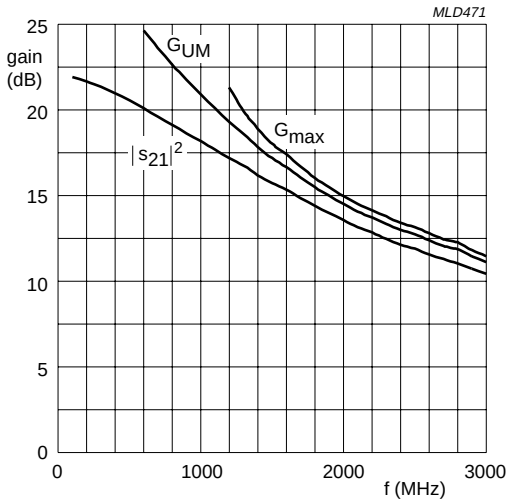
Fig.2 Application circuit.

List of components (see Fig.2**)**

COMPONENT	DESCRIPTION	TYPICAL APPLICATION	HIGH IP3 APPLICATION	DIMENSIONS
C1, C2	multilayer ceramic chip capacitor	100 pF	100 pF	0603
C3, C5	multilayer ceramic chip capacitor	22 nF	22 nF	0603
C4	multilayer ceramic chip capacitor	–	–	–
C6	multilayer ceramic chip capacitor	–	100 nF	0805
L1	SMD inductor	–	3.9 nH	0603
L2	SMD inductor	–	3.9 nH	0603

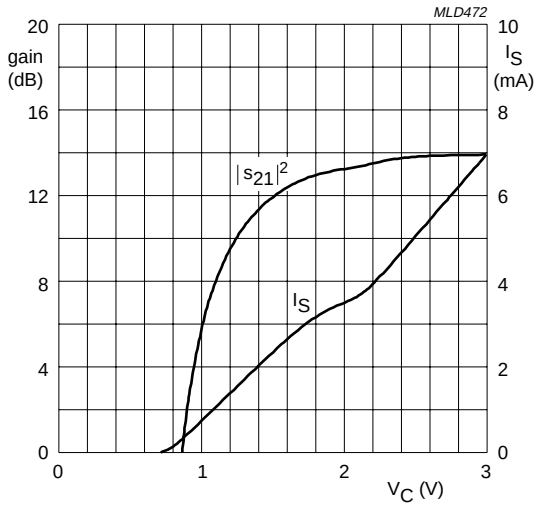
Note

1. The stripline (w = 0.7 mm) is on a gold plated double copper-clad printed-circuit board (ε_r = 6.15), board thickness = 0.64 mm, copper thickness = 35 μm, gold thickness = 5 μm.



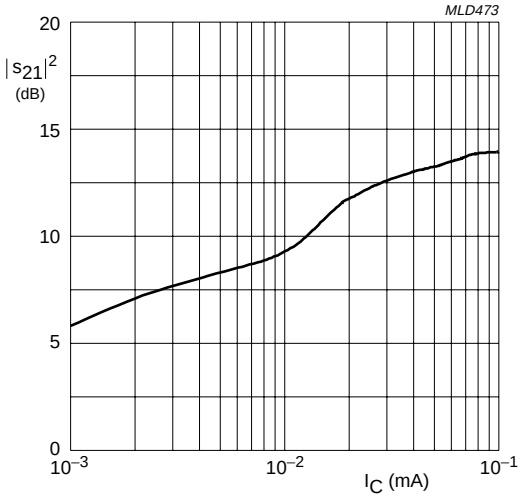
I_C = 7 mA; V_S = V_C = 3 V; P_D = –30 dBm; Z_o = 50 Ω.

Fig.3 Insertion gain ($|s_{21}|^2$), G_{UM} and G_{max} as functions of frequency; typical values.



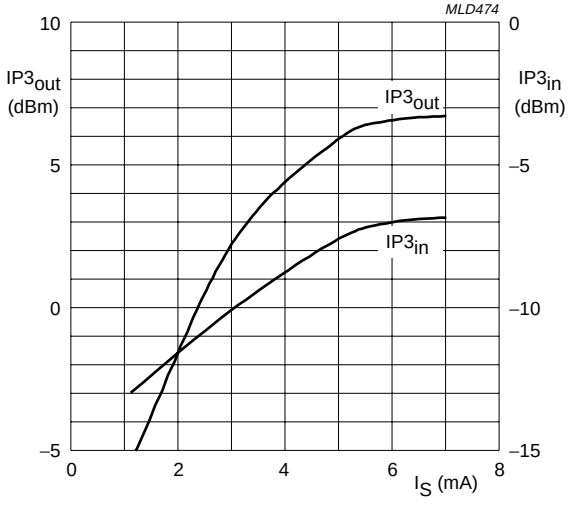
f = 1900 MHz; V_S = 3 V; P_D = –30 dBm.

Fig.4 Insertion gain and supply current as functions of control voltage; typical values.



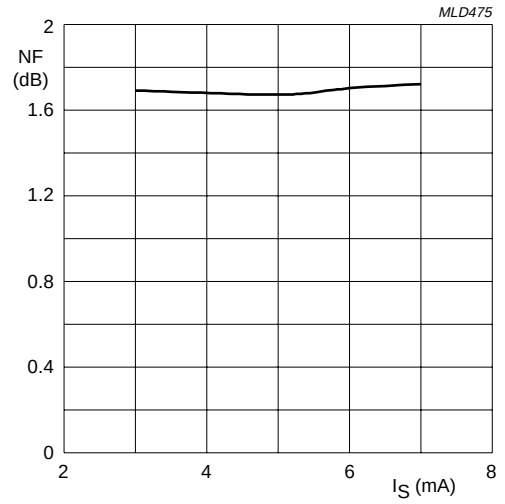
f = 1900 MHz; V_S = 3 V; P_D = –30 dBm.

Fig.5 Insertion gain as a function of control current; typical values.



V_S = V_C = 3 V; P_D = –30 dBm (both tones); f = 1900 MHz; Δf = 100 kHz.

Fig.6 Output and input 3rd order intercept point as functions of supply current; typical application; typical values.



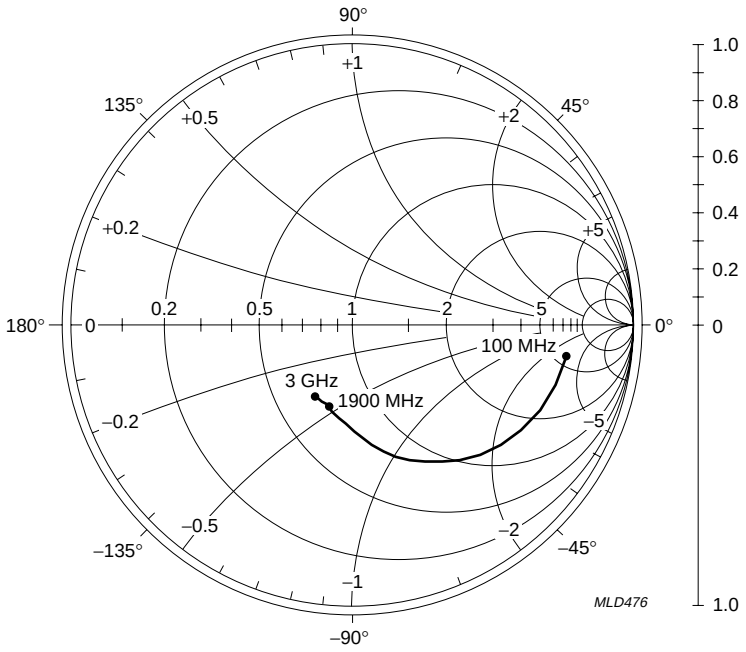
$V_S = V_C = 3$ V; f = 1900 MHz.

Fig.7 Noise figure as a function of supply current; typical values.

Scattering parameters

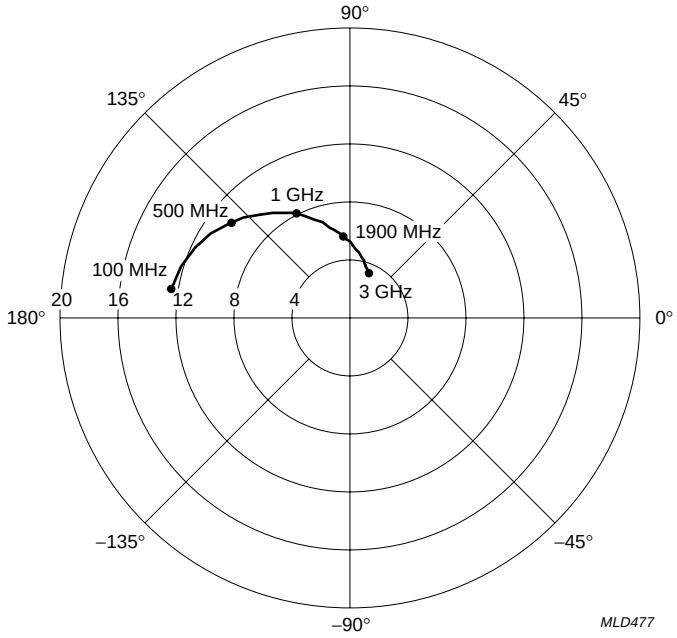
$V_S = V_C = 3$ V; $P_D = -30$ dBm; $Z_o = 50\ \Omega$; $T_{amb} = 25\ ^\circ C$

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
100	0.775	–8.390	12.527	171.1	0.005	84.90	0.742	–6.684
200	0.761	–16.37	12.154	163.1	0.011	79.39	0.731	–13.15
400	0.709	–31.51	11.213	148.6	0.020	72.23	0.689	–24.85
600	0.646	–44.97	10.139	136.4	0.028	66.03	0.631	–34.90
800	0.581	–56.47	9.061	126.1	0.034	61.82	0.573	–43.40
1000	0.519	–66.59	8.131	117.3	0.039	58.86	0.519	–50.54
1200	0.461	–75.41	7.254	109.5	0.043	58.07	0.469	–57.19
1400	0.401	–83.99	6.461	103.1	0.047	57.92	0.428	–64.08
1600	0.350	–93.12	5.869	96.39	0.051	57.26	0.396	–70.03
1800	0.313	–102.0	5.256	90.46	0.054	57.37	0.369	–75.33
2000	0.289	–110.6	4.778	85.58	0.058	58.10	0.348	–80.47
2200	0.278	–118.5	4.394	81.16	0.062	57.66	0.336	–85.37
2400	0.276	–125.0	4.051	77.28	0.066	56.08	0.333	–89.83
2600	0.286	–131.9	3.793	74.34	0.072	60.98	0.316	–92.61
2800	0.293	–136.5	3.571	70.27	0.076	60.21	0.308	–94.44
3000	0.287	–141.6	3.326	67.39	0.083	61.36	0.272	–99.52



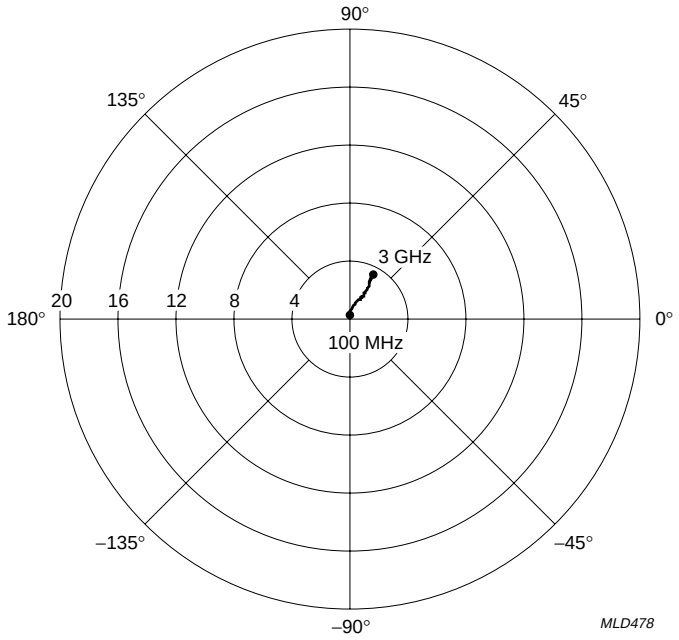
I_C = 7 mA; V_S = V_C = 3 V; P_D = –30 dBm; Z_o = 50 Ω.

Fig.8 Common emitter input reflection coefficient (s_{11}); typical values.



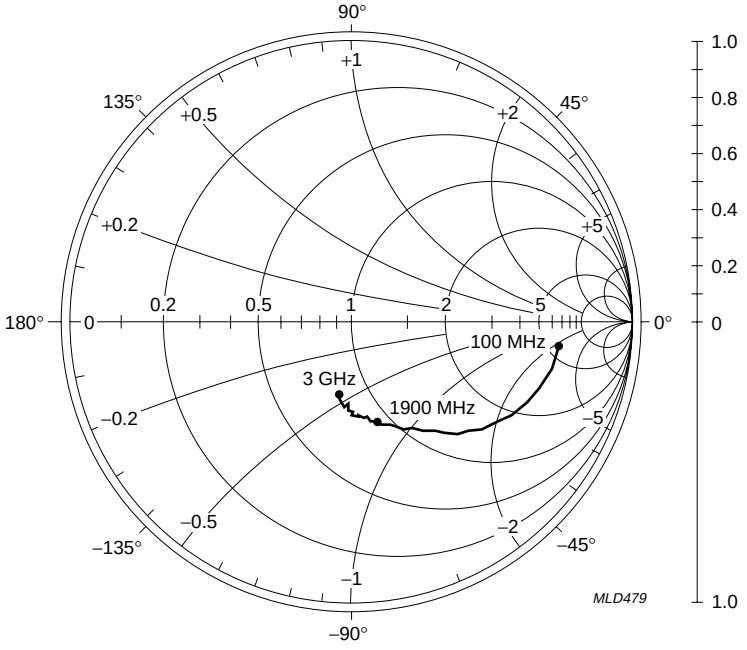
I_C = 7 mA; V_S = V_C = 3 V; P_D = –30 dBm; Z_o = 50 Ω.

Fig.9 Common emitter forward transmission coefficient (s_{21}); typical values.



I_C = 7 mA; V_S = V_C = 3 V; P_D = –30 dBm; Z_o = 50 Ω.

Fig.10 Common emitter reverse transmission coefficient (s_{12}); typical values.

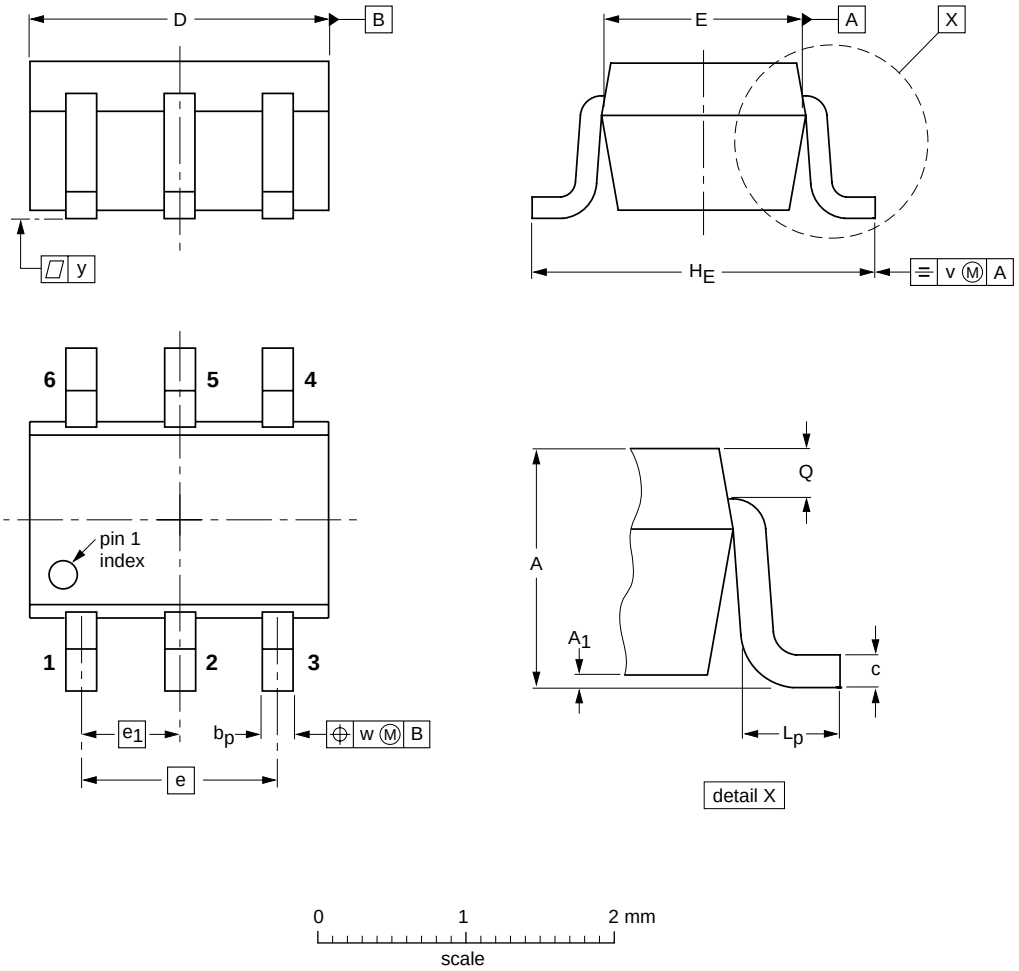


I_C = 7 mA; V_S = V_C = 3 V; P_D = –30 dBm; Z_o = 50 Ω.

Fig.11 Common emitter output reflection coefficient (s_{22}); typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28

DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS (1)
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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